

[TITLE OF THE INVENTION]

A Semiconductor Device and a Method for
Manufacturing Thereof

[Field of the Invention]

The present invention relates to a
5 semiconductor device, a part of which is irradiated by
radiating rays, more specifically, a technology for
radiating a part of the semiconductor.

[Background art]

An insulated gate bipolar transistor
10 (hereinafter referred to as IGBT) 80 shown in Fig. 9 is
known as a semiconductor device having a planar type high
voltage-proof vertical element. The IGBT 80 is a
semiconductor device which has both a high input
impedance characteristic observed in a metal oxide field
15 effect transistor (hereinafter referred to as MOSFET) and
a low saturation voltage characteristic known as a
characteristic of a bipolar transistor.

see C1
C1 7
A substrate 82 used for the IGBT 80 includes a
drain layer 3 with P⁺ type, an n⁺ type layer 5 and an n⁻
20 type layer 7. Base regions 21 are formed in the n⁻ type
layer 7, and source regions 23 with n⁺ type are formed
within the base regions 21. Surface of the n⁻ type
semiconductor layer 82 is covered with a gate oxidation
layer 17.

25 Incidentally, a loss caused by switching arises
see C2

CUT C3

as a result of a parasitic diode generated on a plane of a PN (positive-negative) junction 59. Japanese Patent laid-open publication No. Hei 7-135214 discloses a technology for selectively radiating electron-beams using 5 a mask 41 shown in Fig. 9 during the manufacturing processes in order to avoid the generation of the parasitic diode. The beams pass through through-holes 43 formed in the mask 41 and irradiated on the IGBT 80. In this way, the life-time of carriers located on the plane 10 of the PN junction 59 where the parasitic diode being generated can be shorten as a result of forming crystal defects 61.

das C3

In the manufacturing processes described above, unexpected variation of the threshold voltage in the IGBT 90 is pointed out because of generation of bremsstrahlung caused by the material of the mask 41 made generally of a heavy metal such as lead and the like.

das C4

Japanese Patent laid-open publication No. Hei 8-227895 discloses another IGBT 90 having layers for 15 restricting electron-beams. As shown in Fig. 10, a layer 69 for restricting the beams made of silicon nitride is 20 formed under a source electrode where requiring restriction of the electron-beams. Generation of the bremsstrahlung is restricted even when the beams are 25 radiated to the IGBT 90 under the condition due to masking of the restriction layer 69.

Ins C5 However, the number of process is increased
because the processes for forming the restriction layers
made of silicon nitride is required in the
conventional method.

5 [Disclosure of the present invention]

Ins C6 It is an object of the present invention to
overcome the above mentioned drawbacks associated with
prior arts, and to provide a semiconductor device and a
method for manufacturing thereof capable of radiating
10 electron-beams to the desired region with simple
processes, while not providing adverse effects caused by
bremsstrahlung even when the electron-beams are radiated.

Ins C7 In accordance with characteristics of the
present invention, there is provided a semiconductor
device comprises:

a substrate having a region to be irradiated
with radiating rays, and

Ins C8 ~~a metal wring layer located on the substrate~~
one of directly and indirectly,

Ins C9 ~~wherein the metal wring layer is made of a~~
light metal,

Ins C10 and wherein the metal wring layer located on
the region to be irradiated is formed thinner than that
formed on regions except for the region to be irradiated.

Ins C11 Also, in accordance with characteristics of the
present invention, there is provided a semiconductor

C11
Conc's

device comprises:

a substrate having a region to be irradiated
with radiating rays, and

scr27
~~a metal wring layer located on the substrate,~~

5 *scr27*
C12 wherein the metal wring layer is made of a
light metal,

scr27
C13 and the metal wring layer is used as a mask for
restricting penetration of the radiating rays into region
except for the region to be irradiated.

10 Further, in accordance with characteristics of
the present invention, there is provided a method for
manufacturing a semiconductor device having a substrate,
and a metal wiring layer located on the substrate, a
region of the substrate being irradiated with radiating
rays, the method comprises the steps of:

entirely forming the metal wiring layer,

removing the metal wiring layer located on the
region to be irradiated, and

20 radiating the radiating rays using the metal
wiring layer being remained as a mask.

While the novel features of the invention are
set forth in a general fashion, both as to organization
and content, the invention will be better understood and
appreciated, along with other objects and features
25 thereof, from the following detailed description taken in
conjunction with the drawings.

[Brief description of the drawings]

Fig. 1 is a sectional view showing part of an IGBT 1 as an embodiment of a semiconductor device in accordance with the present invention.

5 Fig. 2 is a perspective view of the IGBT 1.

Fig. 3 is a graph showing a relationship between a range of electrons in the source electrode 22 and energy amount of the electron-beams.

10 Fig. 4A through Fig. 4C are sectional views showing the manufacturing process of the IGBT 1.

~~Fig. 5A and Fig. 5B are another sectional views showing the manufacturing process of the IGBT 1.~~

~~Fig. 6A and Fig. 6B are far another sectional views showing the manufacturing process of the IGBT 1.~~

~~15 Fig. 7A and Fig. 7B are still another sectional views showing the manufacturing process of the IGBT 1.~~

Fig. 8 is yet another sectional view showing the manufacturing process of the IGBT 1.

20 Fig. 9 is a sectional view of the IGBT 80 in the conventional technology.

Fig. 10 is a sectional view of another IGBT 90 in the conventional technology.

[The best mode of preferred embodiment to carry out the present invention]

25 An embodiment of the present invention will be described herein with reference to the drawings. Fig. 1

is a sectional view showing part of an IGBT 1 as one embodiment of a semiconductor device in accordance with the present invention.

Jno 7 C17 5 The IGBT 1 is formed in a substrate 2 for a semiconductor device. In the substrate 2, an n⁺ type layer 5 and an n⁻ type layer 7 are consecutively formed on a drain layer 3 with P⁺ type. A base region 21 with P⁺ type is formed in the n⁻ type layer 7. Source regions 23 are formed in the base region 21. The surface of the n⁻ type layer 7 is covered with a gate oxidation layer 15. A gate electrode 17 is formed on the gate oxidation layer 15. The gate electrode 17 is covered with an inter-insulating layer 19, and a source electrode 22 made of aluminum is formed on the inter-insulating layer 19. 10 15 The source electrode 22 formed as a wiring layer made of a metal is also used for electrically connecting with the source regions 23 in the IGBT element. A passivation layer 29 covers entire surface of the source electrode 22. The first conductive type and the second conductive type are respectively defined as n type and p type in 20 25 this embodiment.

Jno 7 C18 A silicon oxidation layer 27 is formed on a region 24 located between the source regions 23 formed within the base regions 21. Further, the source electrode 22 is not existed at upper part of the silicon oxidation layer 27, and an opening 25 is located on the 25

C14 C15 C16 C17 C18 C19 C20

silicon oxidation layer 27. On the other hand, a crystal defect region 11 is formed at a position in the n⁺ type layer 7 and below the silicon oxidation layers 27.

C14 C15 C16 C17 C18 C19 C20

Fig. 2 is a perspective view of the IGBT 1 before forming the passivation layer 29. As described, the silicon oxidation layer 27 is formed above of the crystal defect region 11, and the opening 25 is located on the silicon oxidation layers 27. In this way, the source electrode 22 made of aluminum can be used both for a wiring, and a mask for the beams.

C14 C15 C16 C17 C18 C19 C20

Next, a method for manufacturing the IGBT 1 will be described. The manufacturing processes similar to an ordinary IGBT are carried out until forming the source electrodes 23. In other words, the substrate 2 is formed by consecutively forming the n⁺ type layer 5 on the drain layer 3 and the n⁻ type layer 7 thereon as shown in Fig. 4A. Thereafter, the gate oxidation layer 15 and the gate electrode 17 are formed successively as shown in Fig. 4B. Ion implantation of P-type impurities is carried out by using the gate electrode 17 as a mask. Further, N-type impurities are implanted ionically by using both a resist layers 81 formed on the gate oxidation layer 15 and the gate oxidation layers 17 as a mask as shown in Fig. 4C. The base region 21 with P⁺ type and a pair of the source regions 23 located in the base region 21 are formed simultaneously by carrying out

thermal treatment as shown in Fig. 5A.

Ins C21

Next, a silicon oxidation (SiO_2) layer 18 is accumulated entirely on the substrate with the chemical vapor deposition (CVD) method as shown in Fig. 5B. A resist layer 82 is formed above of both the crystal defect region 11 and the gate electrode 17 as shown in Fig. 6A. Both the inter-insulation layer 19 and the silicon oxidation layer 27 are formed with an etch-back technique by using the resist layers 82. In this way, the silicon oxidation layer 27 is formed above of the crystal defect region 11 as shown in Fig. 6B.

Next, aluminum is accumulated entirely on the substrate in thickness of 5 μm with CVD method as shown in Fig. 7A.

As shown in Fig. 7B, the source region 22 is formed by carrying out etching using a resist layer 84 being formed. As a result of the etching, the opening 25 is formed on the silicon oxidation layer 27.

The crystal defect region 11 is irradiated by the electron-beams radiated from the above after removing the resist layer 84 as shown in Fig. 8. The radiation of the beams is carried out at 1 mega electro-volts in energy strength in this embodiment.

Ins C22

By carrying out the radiation, the crystal defect region 11 uncovered with the source electrode 22 is irradiated by the beams, so that desired crystal

(C22 conc.)

defects are generated within the region 11. On the other hand, less amount of the beams are irradiated to regions existing outside of the region 11. Although, a certain amounts of crystal defects are generated in the regions 5 existing the outside of the region 11, these defects can be removed by annealing carried out later. In this way, the IGBT 1 shown in Fig. 1 is manufactured.

ens C22

C22

Next, thickness of the source electrode 22 is described hereunder with reference to a relationship between a range of electrons in the source electrode 22 and energy amount of the beams. As shown in Fig. 3, the range of electrons in aluminum is increased when a higher energy is radiated. Usually, energy strength of the beams forming the crystal defect region is in a range from 600 electro-volts to 1 mega electro-volts. The source electrode 22 in thickness of 0.6 cm to 1 cm is required in order to restrict the generation of the crystal defect region with the source electrode 22 alone. However, the source electrode 22 relatively thicker than 15 an ordinary aluminum wiring having a range from 1 μm to 20 10 μm is able to restrict the beams because the beams are restricted by the gate electrode 17, the passivation layer 19 and other layers formed thereunder.

ens C22

C22

Further, the generation of the bremsstrahlung caused by the source electrode 22 made of a heavy metal can be avoided even when the beams are directly radiated

to the source electrode 22 exposed to the air. Because the source electrode 22 is made of a light metal in this embodiment. In this way, only a desired region can be irradiated with the beams by using the source electrode 5 made of aluminum capable of using both as a wiring and a mask for the beams as a result of making an opening at a region to be irradiated without forming a layer for restricting beams in addition to the layers described above.

10 Although, the beams are radiated after removing the resist layer 84, the radiation can be carried out without removing the resist layer 84.

15 Although, the present invention is applied to the IGBT in the embodiments described above, the present invention is also applicable to other types of semiconductors such as a power MOSFET transistor and the like used as a vertical type MOSFET. Further, the present invention can also be used in any semiconductor devices such as ordinary bipolar transistor or others as 20 long as the semiconductor requires the radiation of the beams to a part of the substrate thereof.

25 *JAC 25* Although, the source electrode 22 is made of aluminum, other light metals not causing bremsstrahlung such as an aluminum silicon and the like can be used for the source electrode 22. Any other metals not causing bremsstrahlung such as copper can be used for the source

*C₂₅
C₁₀* electrode 22. Because of its higher density than that of aluminum, the use of copper allows the radiation of the beams to the desired region even when its profile is in a thin form. Further, tungsten can also be used for the source electrode 22.

5

Although, the IGBT is employed as a semiconductor having the region to be irradiated in the embodiment described above, the present invention can be applied to a semiconductor device having the IGBT.

*10
C₂₆* Further, the silicon oxidation layer 27 is provided in order to form the opening 25 located above of the crystal defect region 11 in the embodiment. However, the opening can be formed directly on the source electrode 22 by carrying out etching thereto without providing the silicon oxidation layer.

C₂₇ The semiconductor device in accordance with the present invention is characterized in that, the metal wring layer is made of a light metal. Therefore, no generation of the bremsstrahlung is observed even when the radiation are radiated. Also, the metal wring layer located on the region to be irradiated is formed thinner than that formed on regions except for the region to be irradiated so as to reach the radiating rays to the region to be irradiated. In this way, the crystal defect region can only be formed in the desired region. As a result, it is possible to provide a semiconductor device

ACQUA 14 50730200

C 27
OACU

capable of radiating the radiating rays to the desired region with simple processes, while not providing adverse effects caused by bremsstrahlung even when the radiating rays are radiated. Also, the semiconductor device in accordance with the present invention is characterized in that, the metal wring layer located on the regions except for the region to be irradiated is formed in a thickness so as not to provide any adverse effect on the regions except for the region to be irradiated. Therefore, it is possible to avoid adverse effect on the regions except for the region to be irradiated.

Further, the semiconductor device in accordance with the present invention is characterized in that, the metal wring layer is made of a light metal, and the metal wring layer is used as a mask for restricting penetration of the radiating rays into region except for the region to be irradiated. Therefore, it is possible to provide a semiconductor device capable of radiating the radiating rays only to the desired region with simple processes, while not providing the adverse effects caused by bremsstrahlung even when the radiating rays are radiated.

The semiconductor device in accordance with the present invention is characterized in that, the semiconductor device is an insulated gate bipolar transistor (IGBT), and the region to be irradiated is a positive-negative junction region where a parasitic diode

is generated. Therefore, it is possible to provide an IGBT capable of overcoming a loss arising at the switching caused by generation of a parasitic diode.

Also, the semiconductor device in accordance
5 with the present invention is characterized in that, the semiconductor device is a MOSFET, and the region to be irradiated is a positive-negative junction region where a parasitic diode is generated. Therefore, it is possible to provide a MOSFET capable of overcoming a loss arising
10 at the switching caused by generation of a parasitic diode with a simple structure.

Further, the method for manufacturing a
15 semiconductor device in accordance with the present invention is characterized in that, the method comprises the steps of entirely forming the metal wiring layer, removing the metal wiring layer located on the region to be irradiated, and radiating the radiating rays using the metal wiring layer being remained as a mask. Therefore,
20 it is possible to provide a semiconductor device capable of radiating the radiating rays only to the desired region with simple processes without causing any adverse effects caused by the bremsstrahlung even when the radiating rays are radiated.

The semiconductor device in accordance with the
25 present invention is characterized in that, the metal wiring layer is made of a metal which prevents the

*C 30
cont'd.*

generation of the bremsstrahlung even when the radiating rays are radiated, and the metal wring layer located on the region to be irradiated is formed thinner than that formed on regions except for the region to be irradiated so as to reach the radiating rays to the region to be irradiated. In this way, the crystal defect region can only be formed in the desired region. As a result, it is possible to provide a semiconductor device capable of radiating the radiating rays only to the desired region with simple processes, while not providing adverse effects caused by the bremsstrahlung even when the radiating rays are radiated.

While the invention has been described in its preferred embodiments, it is to be understood that the words which have been used are words of description rather than limitation and that changes within the purview of the appended claims can be made without departing from the true scope and spirit of the invention in its broader aspects.